

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (Ultra High speed U-MOSIII)

# TPCA8003-H

High Speed and High Efficiency DC-DC Converters  
 Notebook PC Applications  
 Portable Equipment Applications

- Small footprint due to small and thin package
- High speed switching
- Small gate charge:  $Q_g = 25 \text{ nC (typ.)}$
- Low drain-source ON resistance:  $R_{DS(ON)} = 5.1 \text{ m}\Omega \text{ (typ.)}$
- High forward transfer admittance:  $|Y_{fs}| = 60\text{S (typ.)}$
- Low leakage current:  $I_{DSS} = 10 \text{ }\mu\text{A (max) (}V_{DS} = 30 \text{ V)}$
- Enhancement mode:  $V_{th} = 1.1 \text{ to } 2.3 \text{ V (}V_{DS} = 10 \text{ V, } I_D = 1 \text{ mA)}$

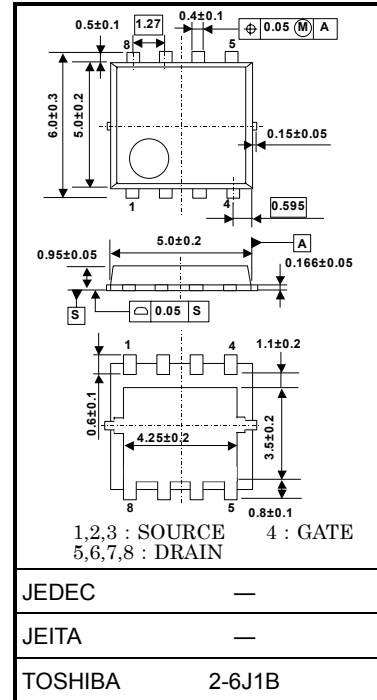
### Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	30	V
Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )		$V_{DGR}$	30	V
Gate-source voltage		$V_{GSS}$	$\pm 20$	V
Drain current	DC (Note 1)	$I_D$	35	A
	Pulsed (Note 1)	$I_{DP}$	105	
Drain power dissipation ( $T_c=25^\circ\text{C}$ )		$P_D$	45	W
Drain power dissipation ( $t = 10 \text{ s}$ ) (Note 2a)		$P_D$	2.8	W
Drain power dissipation ( $t = 10 \text{ s}$ ) (Note 2b)		$P_D$	1.6	W
Single pulse avalanche energy (Note 3)		$E_{AS}$	159	mJ
Avalanche current		$I_{AR}$	35	A
Repetitive avalanche energy ( $T_c=25^\circ\text{C}$ ) (Note 4)		$E_{AR}$	4.5	mJ
Channel temperature		$T_{ch}$	150	°C
Storage temperature range		$T_{stg}$	-55 to 150	°C

Note: For (Note 1), (Note 2), (Note 3), (Note 4), please refer to the next page.

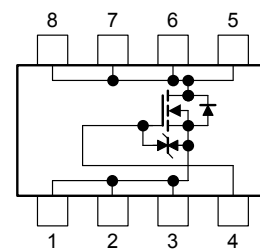
This transistor is an electrostatic sensitive device. Please handle with caution.

Unit: mm



Weight: 0.080 g (typ.)

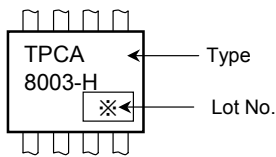
### Circuit Configuration



## Thermal Characteristics

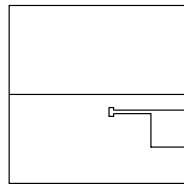
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case ( $T_c=25^\circ\text{C}$ )	$R_{th(ch-c)}$	2.78	$^\circ\text{C/W}$
Thermal resistance, channel to ambient ( $t = 10\text{ s}$ ) (Note 2a)	$R_{th(ch-a)}$	44.6	$^\circ\text{C/W}$
Thermal resistance, channel to ambient ( $t = 10\text{ s}$ ) (Note 2b)	$R_{th(ch-a)}$	78.1	$^\circ\text{C/W}$

## Marking (Note 5)



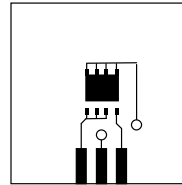
Note 1: Please use devices on condition that the channel temperature is below  $150^\circ\text{C}$ .

Note 2: (a) Device mounted on a glass-epoxy board (a)      (b) Device mounted on a glass-epoxy board (b)



(a)

FR-4  
 $25.4 \times 25.4 \times 0.8$   
 (Unit: mm)



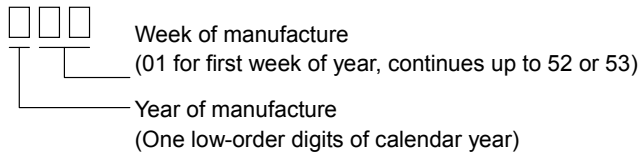
(b)

FR-4  
 $25.4 \times 25.4 \times 0.8$   
 (Unit: mm)

Note 3:  $V_{DD} = 24\text{ V}$ ,  $T_{ch} = 25^\circ\text{C}$  (initial),  $L = 0.1\text{ mH}$ ,  $R_G = 25\ \Omega$ ,  $I_{AR} = 35\text{ A}$

Note 4: Repetitive rating: pulse width limited by max channel temperature

Note 5: \* Weekly code: (Three digits)

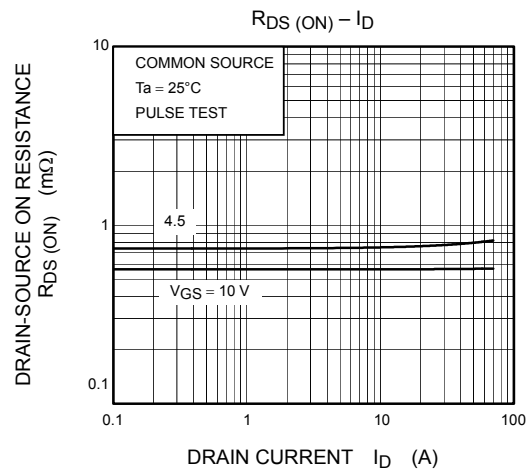
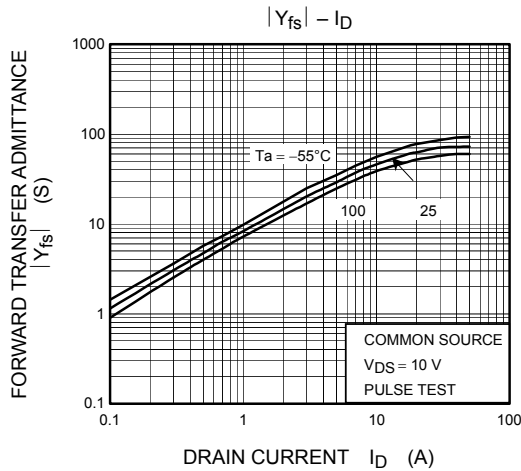
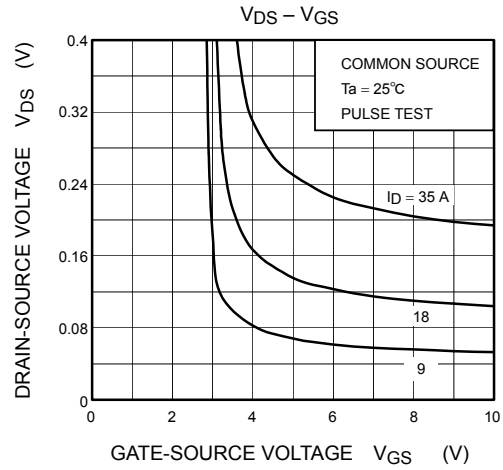
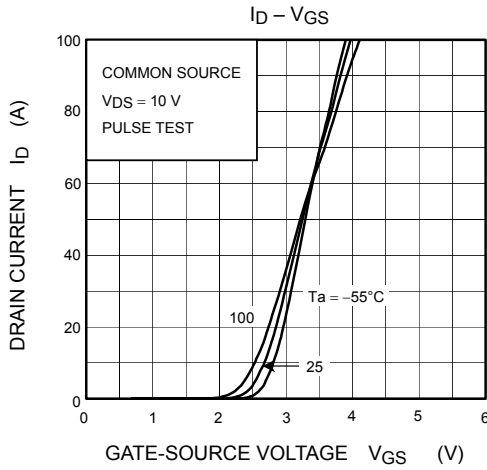
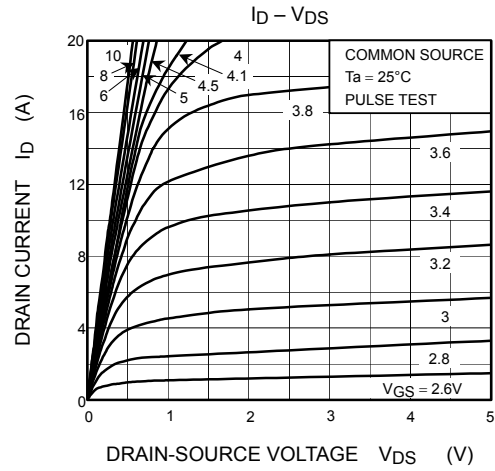
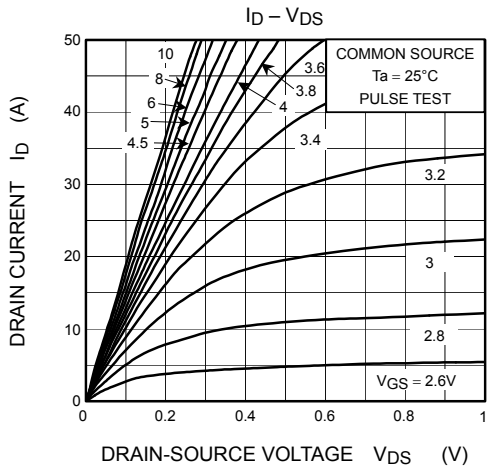


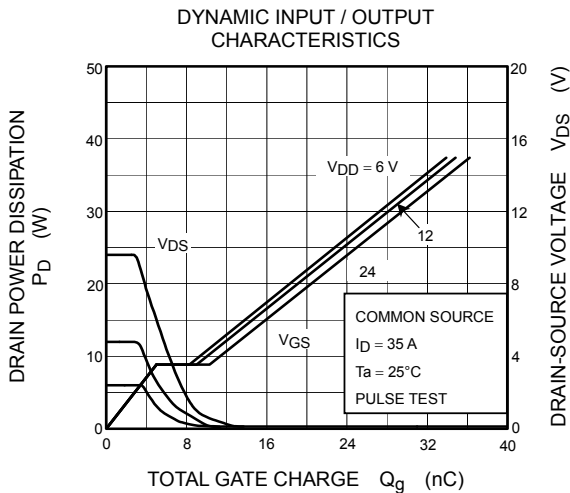
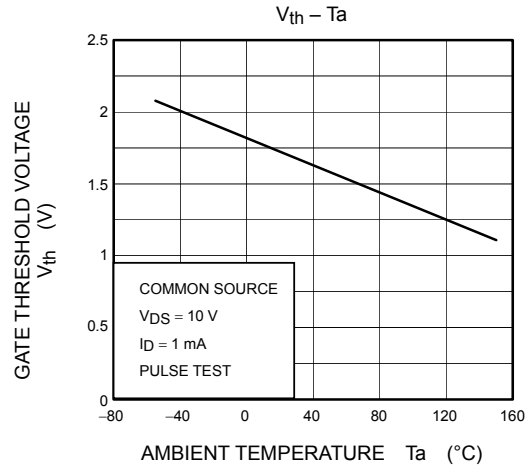
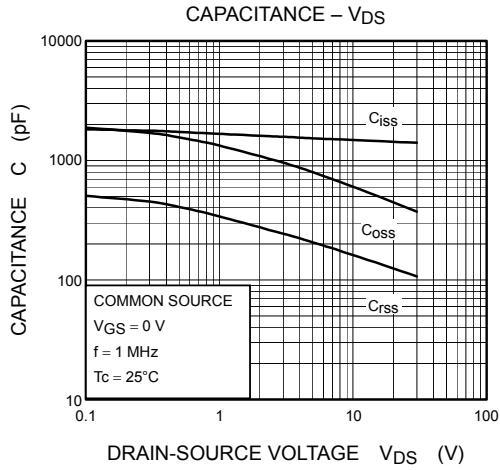
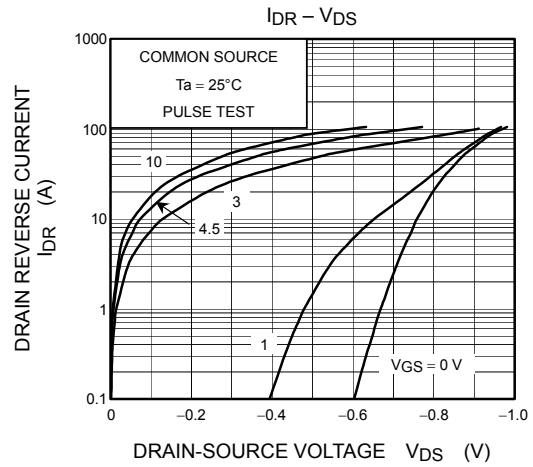
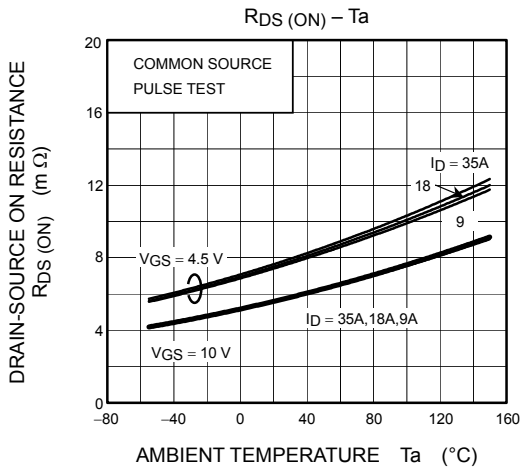
## Electrical Characteristics (Ta = 25°C)

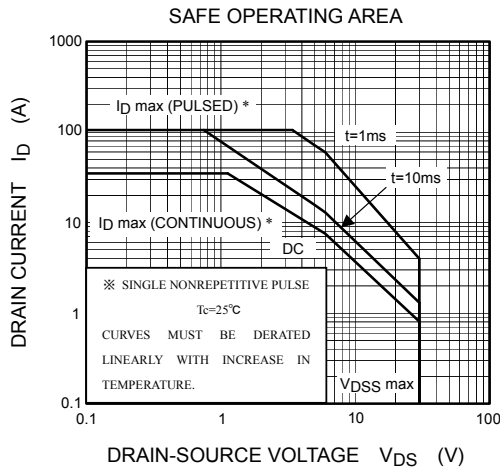
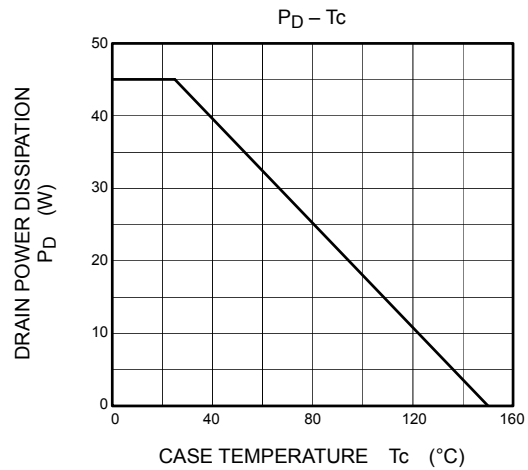
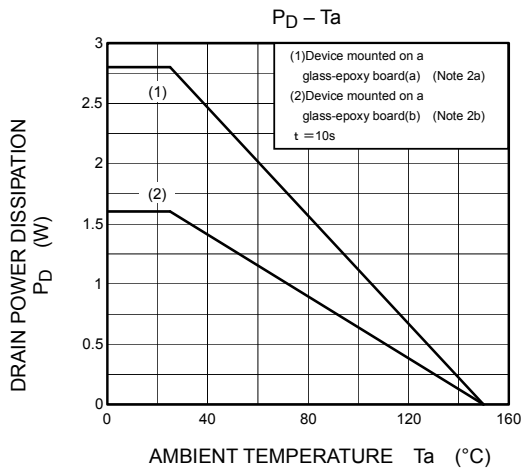
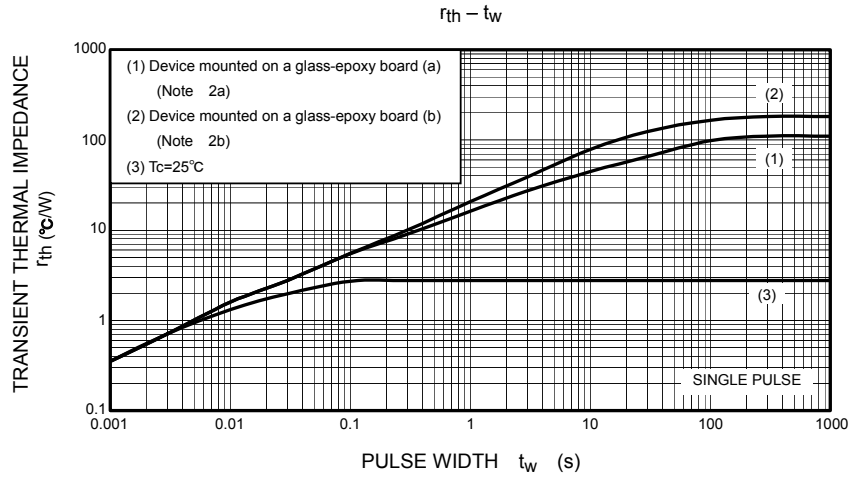
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		$I_{GSS}$	$V_{GS} = \pm 16\text{ V}, V_{DS} = 0\text{ V}$	—	—	$\pm 10$	$\mu\text{A}$
Drain cut-OFF current		$I_{DSS}$	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$	—	—	10	$\mu\text{A}$
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	30	—	—	V
		$V_{(BR)DSX}$	$I_D = 10\text{ mA}, V_{GS} = -20\text{ V}$	15	—	—	
Gate threshold voltage		$V_{th}$	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$	1.1	—	2.3	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 4.5\text{ V}, I_D = 18\text{ A}$	—	7.3	9.5	$\text{m}\Omega$
			$V_{GS} = 10\text{ V}, I_D = 18\text{ A}$	—	5.1	6.6	
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10\text{ V}, I_D = 18\text{ A}$	30	60	—	S
Input capacitance		$C_{iss}$	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	1465	—	pF
Reverse transfer capacitance		$C_{rss}$		—	175	—	
Output capacitance		$C_{oss}$		—	610	—	
Switching time	Rise time	$t_r$	<p><math>V_{GS} = 10\text{ V}</math> <math>0\text{ V}</math></p> <p><math>I_D = 18\text{ A}</math></p> <p><math>V_{OUT}</math></p> <p><math>4.7\Omega</math></p> <p><math>R_L = 0.83\Omega</math></p> <p><math>V_{DD} \approx 15\text{ V}</math></p> <p>Duty <math>\leq 1\%</math>, <math>t_w = 10\ \mu\text{s}</math></p>	—	4	—	ns
	Turn-ON time	$t_{on}$		—	11	—	
	Fall time	$t_f$		—	10	—	
	Turn-OFF time	$t_{off}$		—	36	—	
Total gate charge (gate-source plus gate-drain)		$Q_g$	$V_{DD} \approx 24\text{ V}, V_{GS} = 10\text{ V}, I_D = 35\text{ A}$	—	25	—	nC
			$V_{DD} \approx 24\text{ V}, V_{GS} = 5\text{ V}, I_D = 35\text{ A}$	—	13	—	
Gate-source charge 1		$Q_{gs1}$	$V_{DD} \approx 24\text{ V}, V_{GS} = 10\text{ V}, I_D = 35\text{ A}$	—	5.8	—	
Gate-drain ("miller") charge		$Q_{gd}$	$V_{DD} \approx 24\text{ V}, V_{GS} = 10\text{ V}, I_D = 35\text{ A}$	—	5.1	—	
Gate switch charge		$Q_{sw}$	$V_{DD} \approx 24\text{ V}, V_{GS} = 10\text{ V}, I_D = 35\text{ A}$	—	8.4	—	

## Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Drain reverse current	Pulse (Note 1)	$I_{DRP}$	—	—	—	105	A
Forward voltage (diode)		$V_{DSF}$	$I_{DR} = 35\text{ A}, V_{GS} = 0\text{ V}$	—	—	-1.2	V







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